

ZXMN10A08G

#### 100V SOT223 N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25 ℃
100V	250mΩ @ V <sub>GS</sub> = 10V	2.9A
	300mΩ @ V <sub>GS</sub> = 6V	2.6A

#### **Features and Benefits**

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

#### **Description**

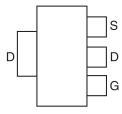
This new generation trench MOSFET from Zetex features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency, power management applications.

#### **Applications**

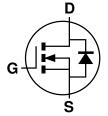
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control



Top View



Pin Out - Top



Equivalent Circuit

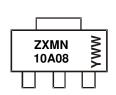
## Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A08GTA	ZXMN10A08	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



SOT223

ZXMN10A08 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}$ W = Week Code (01~53)



## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (VGS=10V; TA = +25 °C) (Note 6)		2.9	
(VGS=10V; TA = +70 °C) (Note 6)	I <sub>D</sub>	2.3	Α
(VGS=10V; TA = +25 °C) (Note 5)		2.0	
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	11	Α
Continuous Source Current (Body Diode) (Note 6)	Is	5	Α
Pulsed Source Current (Body Diode) (Note 7)	Ism	11	A

## Thermal Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at TA = +25 °C (Note 5) Linear Derating Factor	P <sub>D</sub>	2.0 16	W mW/℃
Power Dissipation at TA = +25 °C (Note 6) Linear Derating Factor	P <sub>D</sub>	3.9 31	W mW/℃
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	32	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	℃

#### Electrical Characteristics (@TA = +25 °C, unless otherwise specified.)

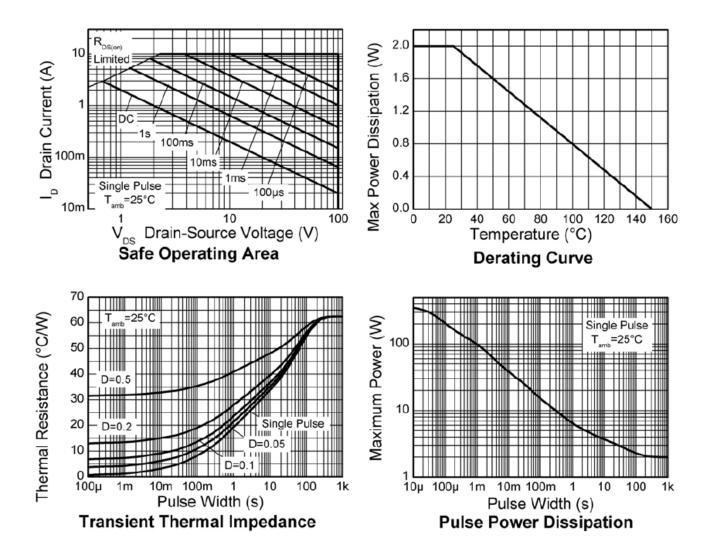
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	0.5	μΑ	V <sub>DS</sub> =100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS	•		•				
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	-	-	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)		_	-	0.25	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A	
Static Drain-Source On-Nesistance (Note 6)	R <sub>DS(ON)</sub>	-	-	0.30	12	$V_{GS} = 6V, I_{D} = 2.6A$	
Forward Transconductance (Notes 8 & 10)	<b>g</b> fs	-	5	-	S	V <sub>DS</sub> = 15V, I <sub>D</sub> =3.2A	
Diode Forward Voltage (Note 8)	VsD	-	0.87	0.95	V	TJ=25 °C, Is=3.2A, VGS=0V	
DYNAMIC CHARACTERISTICS (Note 10)		I .		I.			
Input Capacitance	C <sub>iss</sub>	-	405	-	pF		
Output Capacitance	Coss	-	28.2	-	pF	$V_{DS} = 50V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	14.2	-	pF		
Turn-On Delay Time (Note 9)	t <sub>D(ON)</sub>	-	3.4	-	ns		
Turn-On Rise Time (Note 9)	t <sub>R</sub>	-	2.2	-	ns	$V_{DD} = 30V$ , $I_D = 1.2A$ , $V_{GS} = 10V$ ,	
Turn-Off Delay Time (Note 9)	t <sub>D(OFF)</sub>	-	8	-	ns	$R_G = 6\Omega$	
Turn-Off Fall Time (Note 9)	t <sub>F</sub>	-	3.2	-	ns	1	
Gate Charge (Note 9)	Qg	-	4.2	-	nC	$V_{DS} = 50V$ , $V_{GS} = 5V$ $I_{D} = 1.2A$	
Total Gate Charge (Note 9)	Qg	-	7.7	-	nC	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V I <sub>D</sub> = 1.2A	
Gate-Source Charge (Note 9)	Qgs	-	1.8	-	nC		
Gate-Drain Charge (Note 9)	Qgd	-	2.1	-	nC		
Reverse Recovery Time	trr	-	27	-	ns	- TJ=25 °C, IS=1.2A, di/dt= 100A/μs	
Reverse Recovery Charge	Qrr	-	32	-	nC		

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR4 PCB measured at t ≤ 10 secs.
- 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02, pulse width 300µs pulse width limited by maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width  ${\le}\,300{\mbox{\sc hs}}$  . Duty cycle  ${\le}\,2\%.$
- 9. Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

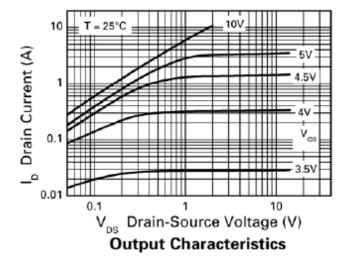


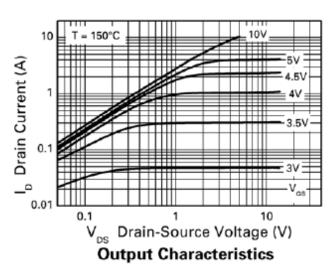
#### **Thermal Characteristics**

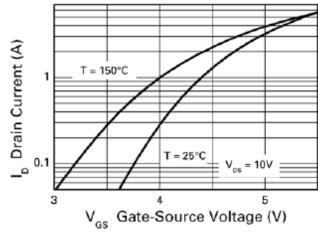


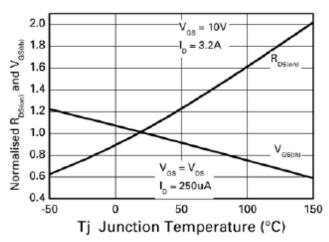


## **Typical Characteristics**

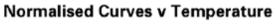


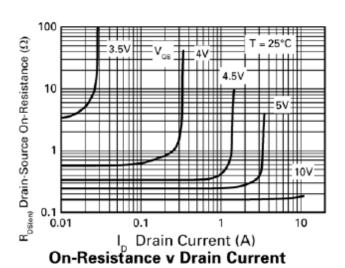


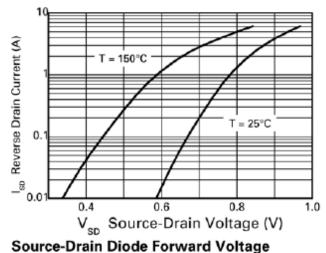




**Typical Transfer Characteristics** 

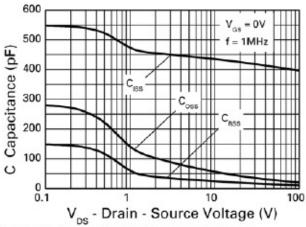






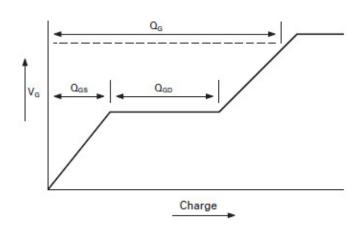


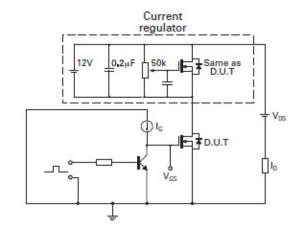
#### Typical Characteristics (continued)



Capacitance v Drain-Source Voltage

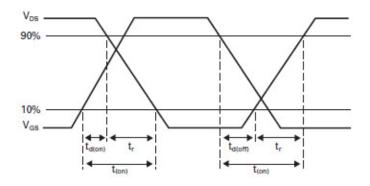
Gate-Source Voltage v Gate Charge

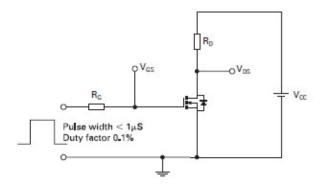




Basic gate charge waveform

Gate charge test circuit





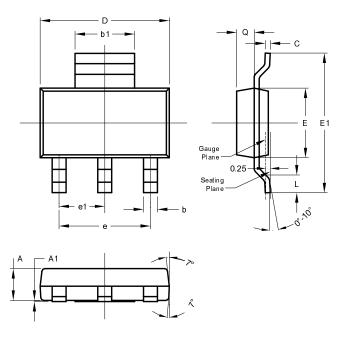
Switching time waveforms

Switching time test circuit



## **Package Outline Dimensions**

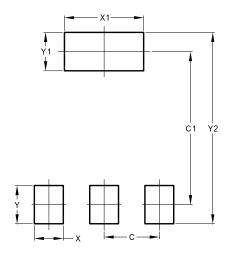
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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